

AMENDMENT TO THE CLAIMS

This listing of claims will replace all prior versions and listings of claims in the application.

Listing of Claims:

1. (Currently amended). A structure having first and second major surfaces comprising:
 - a carrier foil forming a first said major surface;
 - an electrically conductive layer on one of the major surfaces of the carrier foil;
 - a dielectric layer located on the electrically conductive layer wherein the dielectric layer having circuitry features; and
 - plated metal conductive circuitry located within the circuitry features wherein the metal conductive circuitry is substantially flush/coplanar with and surrounded by the dielectric layer,
 - wherein said metal/dielectric co-plane forms said second major surface.
2. (Original). The structure of claim 1 wherein the circuitry features in the dielectric layer are formed completely thru it to the conductive layer.
3. (Original). The structure of claim 1 wherein the circuitry features in the dielectric layer are formed short of the conductive layer.
4. (Original). The structure of claim 1 wherein the conductive circuitry comprised lines of about 0.5 to about 1 mil wide and being about 0.5 to about 3 mils spaced apart.
5. (Original). The structure of claim 1 wherein the metal conductive circuitry comprise copper.

6. (Original). The structure of claim 1 wherein the dielectric layer comprises an epoxy resin or polyimide resin.

7. (Original). The structure of claim 1 wherein the carrier foil comprises copper.

8. (Original). The structure of claim 1 wherein the electrically conductive layer comprises chromium.

9. (Original). The structure of claim 1 wherein the flush metal conductive circuitry is covered with gold or nickel-gold.

10. (Original). The structure of claim 1 wherein the flush metal conductive circuitry is selectively covered with gold or nickel-gold.

11. (Original). The structure of claim 10 wherein gold wire bond attach exist between gold covered circuitry and other components or circuitry features attached to the structure.

12. (Original). The structure of claim 1 wherein a cavity exist thru the dielectric layer to the electrically conductive layer wherein said cavity resides an electronic component.

13. (Original). The structure of claim 1 wherein the structure is attached to a stiffening dielectric layer.

14. (Original). A structure comprising repetitive layers of a structure of claim 1 attached together by a dielectric layer.

15. (Original). The structure of claim 14 comprising interconnects from any layer of a conductive metal circuitry to any other layer of conductive metal circuitry.

16. (Original). The structure of claim 1 comprising flush metal conductive circuitry interconnects from any via in the structure to any other via in the structure.

17. (Currently amended). A structure, having first and second major surfaces, comprising a dielectric base layer; a second dielectric layer containing circuitry features located upon the base dielectric layer; and plated metal conductive circuitry located within the circuitry features wherein the metal conductive circuitry is substantially flush/coplanar with and surrounded by the second dielectric layer, and wherein said metal circuitry/dielectric co-plane form at least one of said major surfaces.

18. (Original). A structure comprising repetitive layers of the structure of claim 17 wherein the conductive circuitry comprises lines of about 0.5 to about 1 mil wide and being about 0.5 to about 3 mils spaced apart and wherein said dielectric base layers is stiffening wherein said layers are attached together by a dielectric layer.

19. (Original). The structure of claim 17 wherein the metal conductive circuitry comprises copper.

20. (Original). The structure of claim 17 wherein the dielectric circuitry containing layer comprises an epoxy resin, polyimide resin or photoimageable dielectric.

21. (Original). The structure of claim 17 wherein the dielectric base layer comprises an epoxy resin, polyimide resin or photoimageable dielectric.

22. (Original). The structure of claim 17 wherein the flushmetal conductive circuitry is covered with gold or nickel-gold.

23. (Original). The structure of claim 22 wherein gold wire bond attach exist between gold covered circuitry and other components or circuitry features attached to the structure.

24. (Original). The structure of claim 17 wherein a cavity exist thru the dielectric layer to the metal conductive layer wherein said cavity resides an electronic component.

25. (Original). The structure of claim 17 wherein the structure is attached to a stiffening dielectric layer.

26. (Original). A structure comprising repetitive layers of the structure in claim 17 attached together by a dielectric layer.

27. (Original). The structure of claim 26 comprising interconnects from any layer of conductive metal circuitry to any other layer of conductive metal circuitry.

28. (Original). The structure of claim 26 comprising flush metal conductive circuitry interconnects from any via in the structure to any other via in the structure.

29. (Original). A structure comprising a dielectric base layer; a second dielectric layer containing circuitry features located upon the base dielectric layer; and metal conductive circuitry located within the circuitry features wherein the metal conductive circuitry is substantially flush/coplanar with and surrounded by the second dielectric layer;

wherein the conductive circuitry comprises lines of about 0.5 to about 1 mil wide and being about 0.5 to about 3 mils spaced apart and circuit features of sufficient size to permit an electronic component to be located in said structure.

30. (Original). The structure of claim 29 wherein said electronic component is an integrated circuit chip and wherein a cavity exists thru the dielectric layer to the metal conductive layer and wherein said integrated circuit chip resides in said cavity.

31. (Original). The structure claim 30 wherein the flush metal conductive circuitry is covered with gold or nickel-gold, and

wherein gold wire bond attach exists between gold covered circuitry and said integrated circuit chip.

32-53 (Canceled).

54. (Withdrawn). The structure obtained by the process of claim 32.